Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	4125
Number of Logic Elements/Cells	33000
Total RAM Bits	1358848
Number of I/O	133
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-BGA
Supplier Device Package	256-FTBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe3-35ea-6ftn256c

MMAC DSP Element

The LatticeECP3 supports a MAC with two multipliers. This is called Multiply Multiply Accumulate or MMAC. In this case, the two operands, AA and AB, are multiplied and the result is added with the previous accumulated value and with the result of the multiplier operation of operands BA and BB. This accumulated value is available at the output. The user can enable the input and pipeline registers, but the output register is always enabled. The output register is used to store the accumulated value. The ALU is configured as the accumulator in the sysDSP slice. A registered overflow signal is also available. The overflow conditions are provided later in this document. Figure 2-28 shows the MMAC sysDSP element.

Figure 2-28. MMAC sysDSP Element

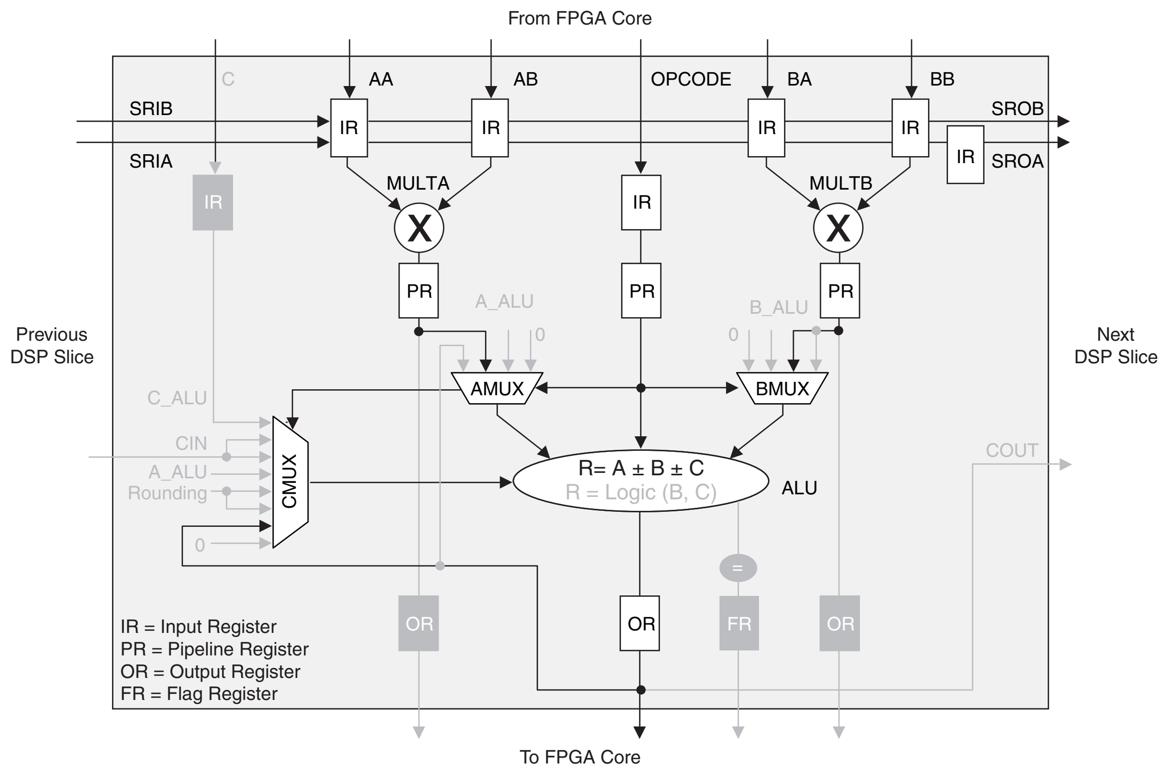
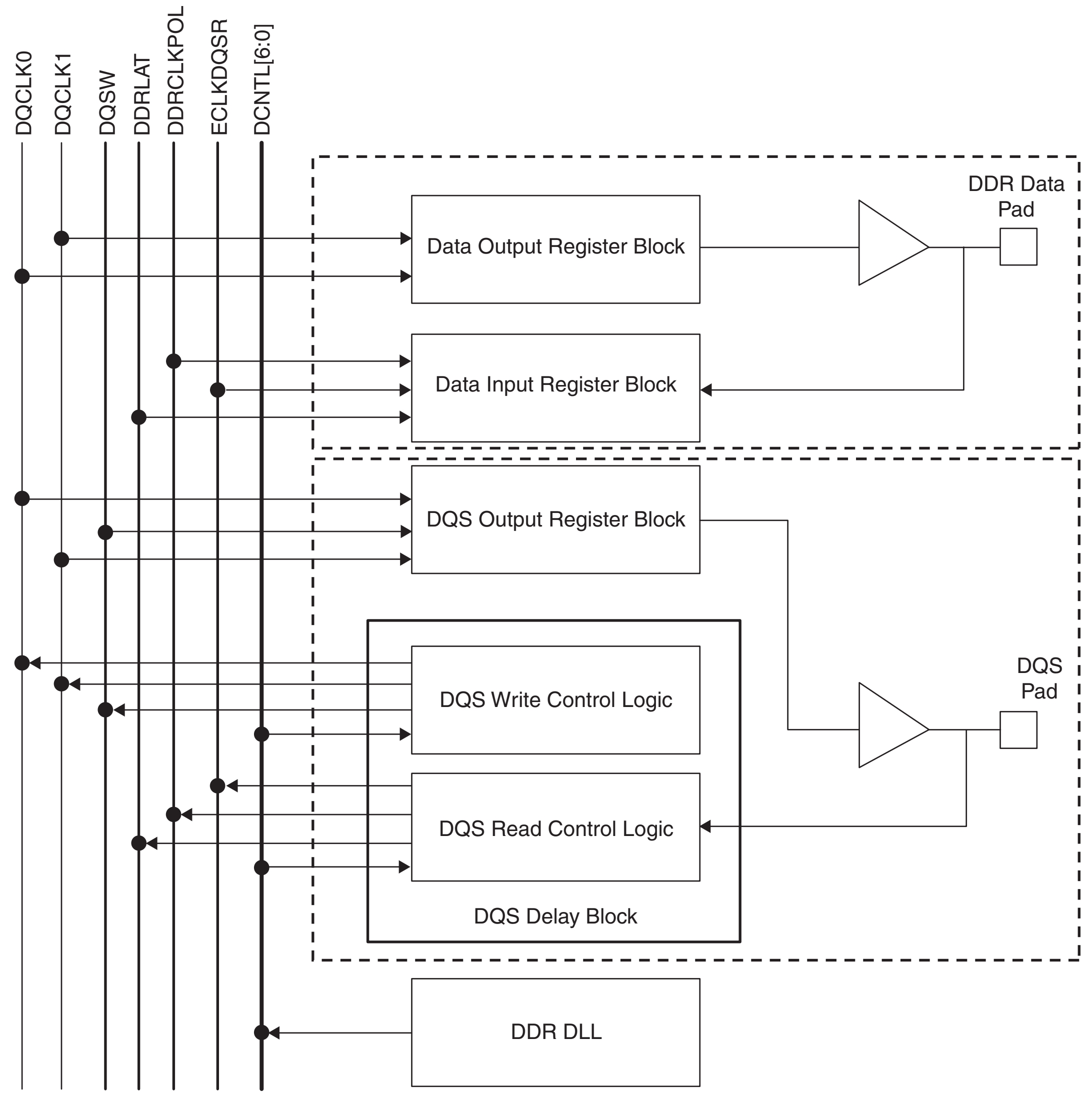


Figure 2-37. DQS Local Bus



Polarity Control Logic

In a typical DDR Memory interface design, the phase relationship between the incoming delayed DQS strobe and the internal system clock (during the READ cycle) is unknown. The LatticeECP3 family contains dedicated circuits to transfer data between these domains. A clock polarity selector is used to prevent set-up and hold violations at the domain transfer between DQS (delayed) and the system clock. This changes the edge on which the data is registered in the synchronizing registers in the input register block. This requires evaluation at the start of each READ cycle for the correct clock polarity.

Prior to the READ operation in DDR memories, DQS is in tristate (pulled by termination). The DDR memory device drives DQS low at the start of the preamble state. A dedicated circuit detects the first DQS rising edge after the preamble state. This signal is used to control the polarity of the clock to the synchronizing registers.

DDR3 Memory Support

LatticeECP3 supports the read and write leveling required for DDR3 memory interfaces.

Read leveling is supported by the use of the DDRCLKPOL and the DDRLAT signals generated in the DQS Read Control logic block. These signals dynamically control the capture of the data with respect to the DQS at the input register block.

To accomplish write leveling in DDR3, each DQS group has a slightly different delay that is set by DYN DELAY[7:0] in the DQS Write Control logic block. The DYN DELAY can set 128 possible delay step settings. In addition, the most significant bit will invert the clock for a 180-degree shift of the incoming clock.

LatticeECP3 input and output registers can also support DDR gearing that is used to receive and transmit the high speed DDR data from and to the DDR3 Memory.

LatticeECP3 supports the 1.5V SSTL I/O standard required for the DDR3 memory interface. For more information, refer to the sysIO section of this data sheet.

Please see TN1180, LatticeECP3 High-Speed I/O Interface for more information on DDR Memory interface implementation in LatticeECP3.

sysI/O Buffer

Each I/O is associated with a flexible buffer referred to as a sysI/O buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysI/O buffers allow users to implement the wide variety of standards that are found in today's systems including LVDS, BLVDS, HSTL, SSTL Class I & II, LVCMOS, LVTTL, LVPECL, PCI.

sysI/O Buffer Banks

LatticeECP3 devices have six sysI/O buffer banks: six banks for user I/Os arranged two per side. The banks on the bottom side are wraparounds of the banks on the lower right and left sides. The seventh sysI/O buffer bank (Configuration Bank) is located adjacent to Bank 2 and has dedicated/shared I/Os for configuration. When a shared pin is not used for configuration it is available as a user I/O. Each bank is capable of supporting multiple I/O standards. Each sysI/O bank has its own I/O supply voltage (V_{CCIO}). In addition, each bank, except the Configuration Bank, has voltage references, V_{REF1} and V_{REF2}, which allow it to be completely independent from the others. Figure 2-38 shows the seven banks and their associated supplies.

In LatticeECP3 devices, single-ended output buffers and ratioed input buffers (LVTTL, LVCMOS and PCI) are powered using V_{CCIO}. LVTTL, LVCMOS33, LVCMOS25 and LVCMOS12 can also be set as fixed threshold inputs independent of V_{CCIO}.

Each bank can support up to two separate V_{REF} voltages, V_{REF1} and V_{REF2}, that set the threshold for the referenced input buffers. Some dedicated I/O pins in a bank can be configured to be a reference voltage supply pin. Each I/O is individually configurable based on the bank's supply and reference voltages.

2. **Left and Right (Banks 2, 3, 6 and 7) sysI/O Buffer Pairs (50% Differential and 100% Single-Ended Outputs)**
   The sysI/O buffer pairs in the left and right banks of the device consist of two single-ended output drivers, two sets of single-ended input buffers (both ratioed and referenced) and one differential output driver. One of the referenced input buffers can also be configured as a differential input. In these banks the two pads in the pair are described as "true" and "comp", where the true pad is associated with the positive side of the differential I/O, and the comp (complementary) pad is associated with the negative side of the differential I/O.

   In addition, programmable on-chip input termination (parallel or differential, static or dynamic) is supported on these sides, which is required for DDR3 interface. However, there is no support for hot-socketing for the I/O pins located on the left and right side of the device as the PCI clamp is always enabled on these pins.

   LVDS, RSDS, PPLVDS and Mini-LVDS differential output drivers are available on 50% of the buffer pairs on the left and right banks.

3. **Configuration Bank sysI/O Buffer Pairs (Single-Ended Outputs, Only on Shared Pins When Not Used by Configuration)**
   The sysI/O buffers in the Configuration Bank consist of ratioed single-ended output drivers and single-ended input buffers. This bank does not support PCI clamp like the other banks on the top, left, and right sides.

   The two pads in the pair are described as "true" and "comp", where the true pad is associated with the positive side of the differential input buffer and the comp (complementary) pad is associated with the negative side of the differential input buffer.

Programmable PCI clamps are only available on the top banks. PCI clamps are used primarily on inputs and bi-directional pads to reduce ringing on the receiving end.

Typical sysI/O I/O Behavior During Power-up

The internal power-on-reset (POR) signal is deactivated when V_{CC}, V_{CCIO8} and V_{CCAUX} have reached satisfactory levels. After the POR signal is deactivated, the FPGA core logic becomes active. It is the user's responsibility to ensure that all other V_{CCIO} banks are active with valid input logic levels to properly control the output logic states of all the I/O banks that are critical to the application. For more information about controlling the output logic state with valid input logic levels during power-up in LatticeECP3 devices, see the list of technical documentation at the end of this data sheet.

The V_{CC} and V_{CCAUX} supply the power to the FPGA core fabric, whereas the V_{CCIO} supplies power to the I/O buffers. In order to simplify system design while providing consistent and predictable I/O behavior, it is recommended that the I/O buffers be powered-up prior to the FPGA core fabric. V_{CCIO} supplies should be powered-up before or together with the V_{CC} and V_{CCAUX} supplies.

Supported sysI/O Standards

The LatticeECP3 sysI/O buffer supports both single-ended and differential standards. Single-ended standards can be further subdivided into LVCMOS, LVTTL and other standards. The buffers support the LVTTL, LVCMOS 1.2 V, 1.5 V, 1.8 V, 2.5 V and 3.3 V standards. In the LVCMOS and LVTTL modes, the buffer has individual configuration options for drive strength, slew rates, bus maintenance (weak pull-up, weak pull-down, or a bus-keeper latch) and open drain. Other single-ended standards supported include SSTL and HSTL. Differential standards supported include LVDS, BLVDS, LVPECL, MLVDS, RSDS, Mini-LVDS, PPLVDS (point-to-point LVDS), TRLVDS (Transition Reduced LVDS), differential SSTL and differential HSTL. For further information on utilizing the sysI/O buffer to support a variety of standards please see TN1177, LatticeECP3 sysIO Usage Guide.

Table 2-14. Available SERDES Quads per LatticeECP3 Devices

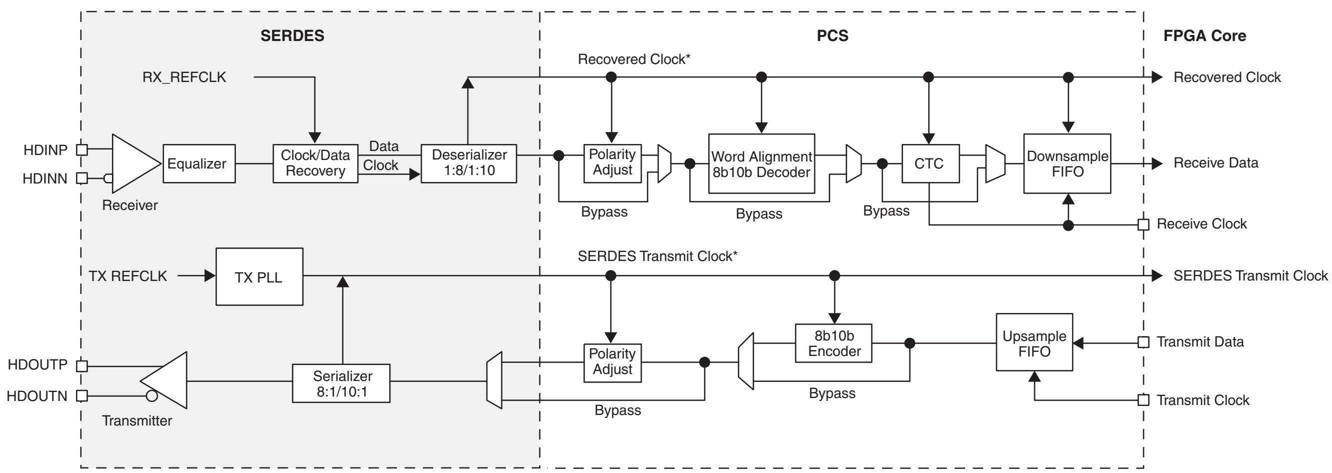
Package	ECP3-17	ECP3-35	ECP3-70	ECP3-95	ECP3-150
256 ftBGA	1	1	—	—	—
328 csBGA	2 channels	—	—	—	—
484 fpBGA	1	1	1	1	
672 fpBGA	—	1	2	2	2
1156 fpBGA	—	—	3	3	4

SERDES Block

A SERDES receiver channel may receive the serial differential data stream, equalize the signal, perform Clock and Data Recovery (CDR) and de-serialize the data stream before passing the 8- or 10-bit data to the PCS logic. The SERDES transmitter channel may receive the parallel 8- or 10-bit data, serialize the data and transmit the serial bit stream through the differential drivers. Figure 2-41 shows a single-channel SERDES/PCS block. Each SERDES channel provides a recovered clock and a SERDES transmit clock to the PCS block and to the FPGA core logic.

Each transmit channel, receiver channel, and SERDES PLL shares the same power supply (VCCA). The output and input buffers of each channel have their own independent power supplies (VCCOB and VCCIB).

Figure 2-41. Simplified Channel Block Diagram for SERDES/PCS Block



PCS

As shown in Figure 2-41, the PCS receives the parallel digital data from the deserializer and selects the polarity, performs word alignment, decodes (8b/10b), provides Clock Tolerance Compensation and transfers the clock domain from the recovered clock to the FPGA clock via the Down Sample FIFO.

For the transmit channel, the PCS block receives the parallel data from the FPGA core, encodes it with 8b/10b, selects the polarity and passes the 8/10 bit data to the transmit SERDES channel.

The PCS also provides bypass modes that allow a direct 8-bit or 10-bit interface from the SERDES to the FPGA logic. The PCS interface to the FPGA can also be programmed to run at 1/2 speed for a 16-bit or 20-bit interface to the FPGA logic.

DC Electrical Characteristics

Over Recommended Operating Conditions

Symbol	Parameter	Condition	Min.	Typ.	Max.	Units
I_{IL}, I_{IH}[1, 4]	Input or I/O Low Leakage	$0 \le V_{IN} \le (V_{CCIO} - 0.2\ V)$	—	—	10	µA
I_{IH}[1, 3]	Input or I/O High Leakage	$(V_{CCIO} - 0.2\ V) < V_{IN} \le 3.6\ V$	—	—	150	µA
I_{PU}	I/O Active Pull-up Current	$0 \le V_{IN} \le 0.7\ V_{CCIO}$	–30	—	–210	µA
I_{PD}	I/O Active Pull-down Current	V_{IL} (MAX) $\le V_{IN} \le V_{CCIO}$	30	—	210	µA
I_{BHLS}	Bus Hold Low Sustaining Current	$V_{IN} = V_{IL}$ (MAX)	30	—	—	µA
I_{BHHS}	Bus Hold High Sustaining Current	$V_{IN} = 0.7\ V_{CCIO}$	–30	—	—	µA
I_{BHLO}	Bus Hold Low Overdrive Current	$0 \le V_{IN} \le V_{CCIO}$	—	—	210	µA
I_{BHHO}	Bus Hold High Overdrive Current	$0 \le V_{IN} \le V_{CCIO}$	—	—	–210	µA
V_{BHT}	Bus Hold Trip Points	$0 \le V_{IN} \le V_{IH}$ (MAX)	V_{IL} (MAX)	—	V_{IH} (MIN)	V
C1	I/O Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = 1.2 V, V_{IO} = 0 to V_{IH} (MAX)	—	5	8	pf
C2	Dedicated Input Capacitance[2]	V_{CCIO} = 3.3 V, 2.5 V, 1.8 V, 1.5 V, 1.2 V, V_{CC} = 1.2 V, V_{IO} = 0 to V_{IH} (MAX)	—	5	7	pf

1. Input or I/O leakage current is measured with the pin configured as an input or as an I/O with the output driver tri-stated. It is not measured with the output driver active. Bus maintenance circuits are disabled.
2. T_A 25 °C, f = 1.0 MHz.
3. Applicable to general purpose I/Os in top and bottom banks.
4. When used as V_{REF}, maximum leakage= 25 µA.

sysI/O Single-Ended DC Electrical Characteristics

Input/Output Standard	V_{IL} Min. (V)	V_{IL} Max. (V)	V_{IH} Min. (V)	V_{IH} Max. (V)	V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL}[1] (mA)	I_{OH}[1] (mA)
LVCMOS33	–0.3	0.8	2.0	3.6	0.4	V_{CCIO} - 0.4	20, 16, 12, 8, 4	–20, –16, –12, -8, –4
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS25	–0.3	0.7	1.7	3.6	0.4	V_{CCIO} - 0.4	20, 16, 12, 8, 4	–20, –16, –12, –8, –4
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS18	–0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.6	0.4	V_{CCIO} - 0.4	16, 12, 8, 4	–16, –12, –8, –4
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS15	–0.3	0.35 V_{CCIO}	0.65 V_{CCIO}	3.6	0.4	V_{CCIO} - 0.4	8, 4	–8, –4
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVCMOS12	–0.3	0.35 V_{CC}	0.65 V_{CC}	3.6	0.4	V_{CCIO} - 0.4	6, 2	–6, –2
					0.2	V_{CCIO} - 0.2	0.1	–0.1
LVTTL33	–0.3	0.8	2.0	3.6	0.4	V_{CCIO} - 0.4	20, 16, 12, 8, 4	–20, –16, –12, –8, –4
					0.2	V_{CCIO} - 0.2	0.1	–0.1
PCI33	–0.3	0.3 V_{CCIO}	0.5 V_{CCIO}	3.6	0.1 V_{CCIO}	0.9 V_{CCIO}	1.5	–0.5
SSTL18_I	–0.3	V_{REF} - 0.125	V_{REF} + 0.125	3.6	0.4	V_{CCIO} - 0.4	6.7	–6.7
SSTL18_II (DDR2 Memory)	–0.3	V_{REF} - 0.125	V_{REF} + 0.125	3.6	0.28	V_{CCIO} - 0.28	8	–8
							11	–11
SSTL2_I	–0.3	V_{REF} - 0.18	V_{REF} + 0.18	3.6	0.54	V_{CCIO} - 0.62	7.6	–7.6
							12	–12
SSTL2_II (DDR Memory)	–0.3	V_{REF} - 0.18	V_{REF} + 0.18	3.6	0.35	V_{CCIO} - 0.43	15.2	–15.2
							20	–20
SSTL3_I	–0.3	V_{REF} - 0.2	V_{REF} + 0.2	3.6	0.7	V_{CCIO} - 1.1	8	–8
SSTL3_II	–0.3	V_{REF} - 0.2	V_{REF} + 0.2	3.6	0.5	V_{CCIO} - 0.9	16	–16
SSTL15 (DDR3 Memory)	–0.3	V_{REF} - 0.1	V_{REF} + 0.1	3.6	0.3	V_{CCIO} - 0.3	7.5	–7.5
						V_{CCIO} * 0.8	9	–9
HSTL15_I	–0.3	V_{REF} - 0.1	V_{REF} + 0.1	3.6	0.4	V_{CCIO} - 0.4	4	–4
							8	–8
HSTL18_I	–0.3	V_{REF} - 0.1	V_{REF} + 0.1	3.6	0.4	V_{CCIO} - 0.4	8	–8
							12	–12
HSTL18_II	–0.3	V_{REF} - 0.1	V_{REF} + 0.1	3.6	0.4	V_{CCIO} - 0.4	16	–16

1. For electromigration, the average DC current drawn by I/O pads between two consecutive V_{CCIO} or GND pad connections, or between the last V_{CCIO} or GND in an I/O bank and the end of an I/O bank, as shown in the Logic Signal Connections table (also shown as I/O grouping) shall not exceed n * 8 mA, where n is the number of I/O pads between the two consecutive bank V_{CCIO} or GND connections or between the last V_{CCIO} and GND in a bank and the end of a bank. IO Grouping can be found in the Data Sheet Pin Tables, which can also be generated from the Lattice Diamond software.

LVPECL33

The LatticeECP3 devices support the differential LVPECL standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The LVPECL input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-3 is one possible solution for point-to-point signals.

Figure 3-3. Differential LVPECL33

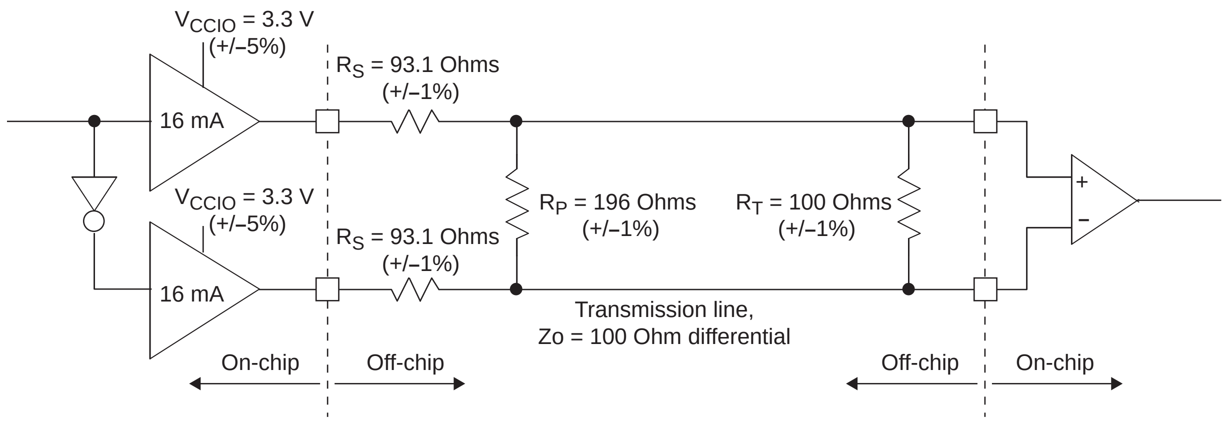


Table 3-3. LVPECL33 DC Conditions[1]

Over Recommended Operating Conditions

Parameter	Description	Typical	Units
V_{CCIO}	Output Driver Supply (+/–5%)	3.30	V
Z_{OUT}	Driver Impedance	10	Ω
R_S	Driver Series Resistor (+/–1%)	93	Ω
R_P	Driver Parallel Resistor (+/–1%)	196	Ω
R_T	Receiver Termination (+/–1%)	100	Ω
V_{OH}	Output High Voltage	2.05	V
V_{OL}	Output Low Voltage	1.25	V
V_{OD}	Output Differential Voltage	0.80	V
V_{CM}	Output Common Mode Voltage	1.65	V
Z_{BACK}	Back Impedance	100.5	Ω
I_{DC}	DC Output Current	12.11	mA

1. For input buffer, see LVDS table.

MLVDS25

The LatticeECP3 devices support the differential MLVDS standard. This standard is emulated using complementary LVCMOS outputs in conjunction with a parallel resistor across the driver outputs. The MLVDS input standard is supported by the LVDS differential input buffer. The scheme shown in Figure 3-5 is one possible solution for MLVDS standard implementation. Resistor values in Figure 3-5 are industry standard values for 1% resistors.

Figure 3-5. MLVDS25 (Multipoint Low Voltage Differential Signaling)

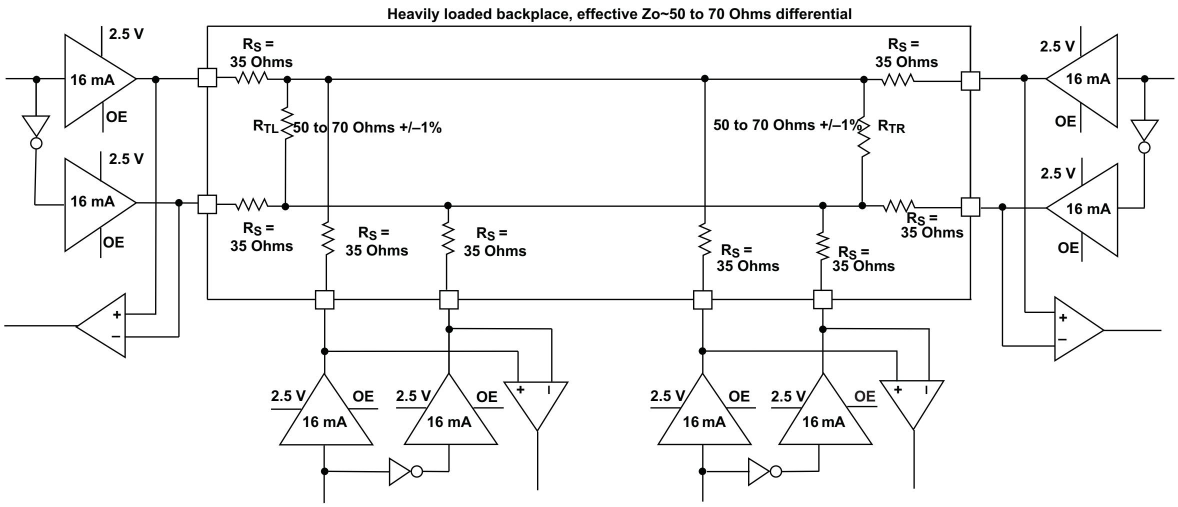


Table 3-5. MLVDS25 DC Conditions[1]

Parameter	Description	Typical		Units
		Zo=50Ω	Zo=70Ω	
V_{CCIO}	Output Driver Supply (+/–5%)	2.50	2.50	V
Z_{OUT}	Driver Impedance	10.00	10.00	Ω
R_S	Driver Series Resistor (+/–1%)	35.00	35.00	Ω
R_{TL}	Driver Parallel Resistor (+/–1%)	50.00	70.00	Ω
R_{TR}	Receiver Termination (+/–1%)	50.00	70.00	Ω
V_{OH}	Output High Voltage	1.52	1.60	V
V_{OL}	Output Low Voltage	0.98	0.90	V
V_{OD}	Output Differential Voltage	0.54	0.70	V
V_{CM}	Output Common Mode Voltage	1.25	1.25	V
I_{DC}	DC Output Current	21.74	20.00	mA

1. For input buffer, see LVDS table.

Typical Building Block Function Performance

Pin-to-Pin Performance (LVCMOS25 12 mA Drive)[1, 2, 3]

Function	–8 Timing	Units
Basic Functions		
16-bit Decoder	4.7	ns
32-bit Decoder	4.7	ns
64-bit Decoder	5.7	ns
4:1 MUX	4.1	ns
8:1 MUX	4.3	ns
16:1 MUX	4.7	ns
32:1 MUX	4.8	ns

1. These functions were generated using the ispLEVER design tool. Exact performance may vary with device and tool version. The tool uses internal parameters that have been characterized but are not tested on every device.
2. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from the Diamond or ispLEVER software.

Register-to-Register Performance[1, 2, 3]

Function	–8 Timing	Units
Basic Functions		
16-bit Decoder	500	MHz
32-bit Decoder	500	MHz
64-bit Decoder	500	MHz
4:1 MUX	500	MHz
8:1 MUX	500	MHz
16:1 MUX	500	MHz
32:1 MUX	445	MHz
8-bit adder	500	MHz
16-bit adder	500	MHz
64-bit adder	305	MHz
16-bit counter	500	MHz
32-bit counter	460	MHz
64-bit counter	320	MHz
64-bit accumulator	315	MHz
Embedded Memory Functions		
512x36 Single Port RAM, EBR Output Registers	340	MHz
1024x18 True-Dual Port RAM (Write Through or Normal, EBR Output Registers)	340	MHz
1024x18 True-Dual Port RAM (Read-Before-Write, EBR Output Registers	130	MHz
1024x18 True-Dual Port RAM (Write Through or Normal, PLC Output Registers)	245	MHz
Distributed Memory Functions		
16x4 Pseudo-Dual Port RAM (One PFU)	500	MHz
32x4 Pseudo-Dual Port RAM	500	MHz
64x8 Pseudo-Dual Port RAM	400	MHz
DSP Function		
18x18 Multiplier (All Registers)	400	MHz
9x9 Multiplier (All Registers)	400	MHz
36x36 Multiply (All Registers)	260	MHz

LatticeECP3 External Switching Characteristics (Continued)[1, 2, 3, 13]

Over Recommended Commercial Operating Conditions

Parameter	Description	Device	–8		–7		–6		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-70EA/95EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-35EA	683	—	688	—	690	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-35EA	683	—	688	—	690	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-35EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-17EA	683	—	688	—	690	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-17EA	683	—	688	—	690	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-17EA	—	250	—	250	—	250	MHz
Generic DDRX1 Output with Clock and Data Aligned at Pin (GDDRX1_TX.SCLK.Aligned)[10]									
$t_{DIBGDDR}$	Data Invalid Before Clock	ECP3-150EA	—	335	—	338	—	341	ps
$t_{DIAGDDR}$	Data Invalid After Clock	ECP3-150EA	—	335	—	338	—	341	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA	—	250	—	250	—	250	MHz
$t_{DIBGDDR}$	Data Invalid Before Clock	ECP3-70EA/95EA	—	339	—	343	—	347	ps
$t_{DIAGDDR}$	Data Invalid After Clock	ECP3-70EA/95EA	—	339	—	343	—	347	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-70EA/95EA	—	250	—	250	—	250	MHz
$t_{DIBGDDR}$	Data Invalid Before Clock	ECP3-35EA	—	322	—	320	—	321	ps
$t_{DIAGDDR}$	Data Invalid After Clock	ECP3-35EA	—	322	—	320	—	321	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-35EA	—	250	—	250	—	250	MHz
$t_{DIBGDDR}$	Data Invalid Before Clock	ECP3-17EA	—	322	—	320	—	321	ps
$t_{DIAGDDR}$	Data Invalid After Clock	ECP3-17EA	—	322	—	320	—	321	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-17EA	—	250	—	250	—	250	MHz
Generic DDRX1 Output with Clock and Data (<10 Bits Wide) Centered at Pin (GDDRX1_TX.DQS.Centered)[10]									
Left and Right Sides									
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-150EA	670	—	670	—	670	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-150EA	670	—	670	—	670	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-150EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-70EA/95EA	657	—	652	—	650	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-70EA/95EA	657	—	652	—	650	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-70EA/95EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-35EA	670	—	675	—	676	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-35EA	670	—	675	—	676	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-35EA	—	250	—	250	—	250	MHz
$t_{DVBGDDR}$	Data Valid Before CLK	ECP3-17EA	670	—	670	—	670	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	ECP3-17EA	670	—	670	—	670	—	ps
f_{MAX_GDDR}	DDRX1 Clock Frequency	ECP3-17EA	—	250	—	250	—	250	MHz
Generic DDRX2 Output with Clock and Data (>10 Bits Wide) Aligned at Pin (GDDRX2_TX.Aligned)									
Left and Right Sides									
$t_{DIBGDDR}$	Data Invalid Before Clock	All ECP3EA Devices	—	200	—	210	—	220	ps
$t_{DIAGDDR}$	Data Invalid After Clock	All ECP3EA Devices	—	200	—	210	—	220	ps
f_{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	—	500	—	420	—	375	MHz
Generic DDRX2 Output with Clock and Data (>10 Bits Wide) Centered at Pin Using DQSDLL (GDDRX2_TX.DQSDLL.Centered)[11]									
Left and Right Sides									
$t_{DVBGDDR}$	Data Valid Before CLK	All ECP3EA Devices	400	—	400	—	431	—	ps
$t_{DVAGDDR}$	Data Valid After CLK	All ECP3EA Devices	400	—	400	—	432	—	ps
f_{MAX_GDDR}	DDRX2 Clock Frequency	All ECP3EA Devices	—	400	—	400	—	375	MHz

Figure 3-6. Generic DDRX1/DDRX2 (With Clock and Data Edges Aligned)

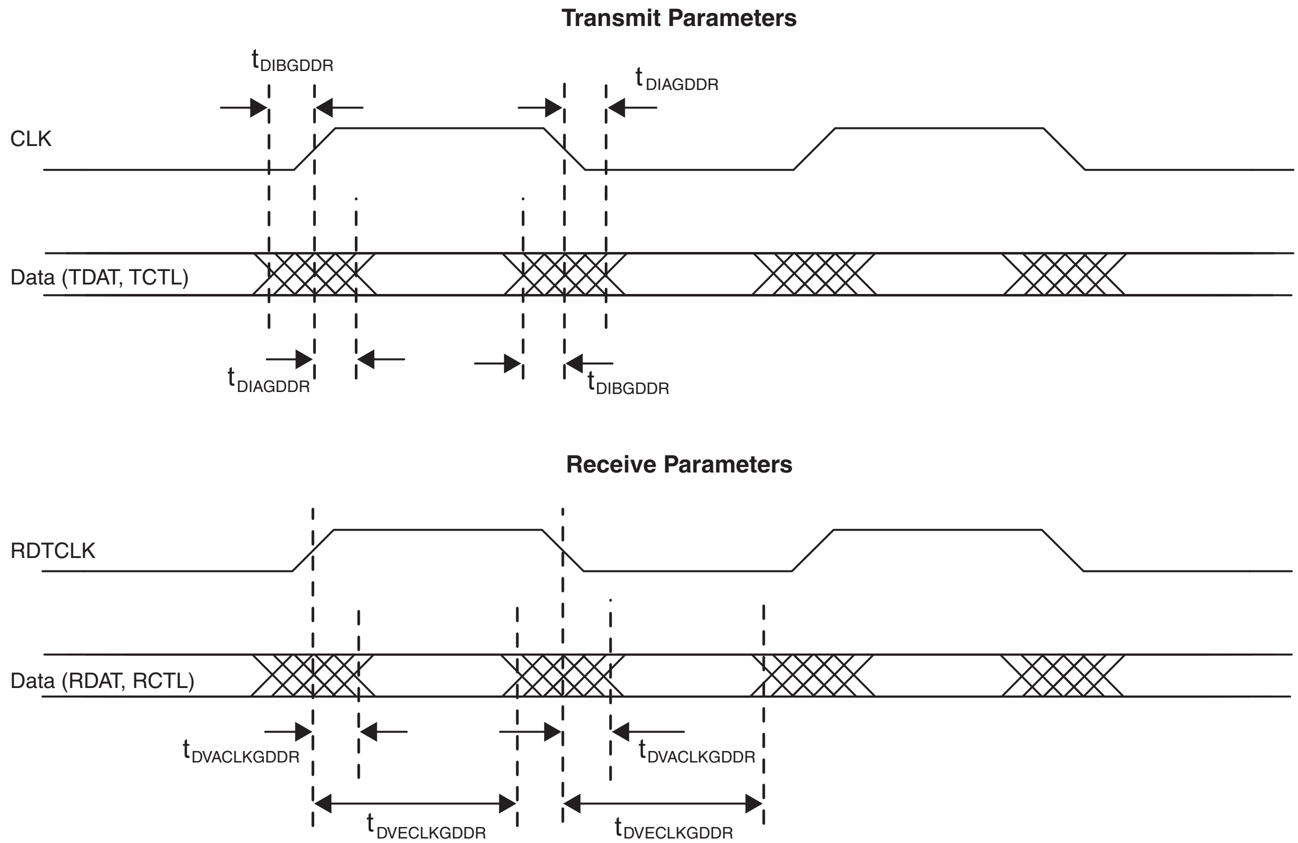
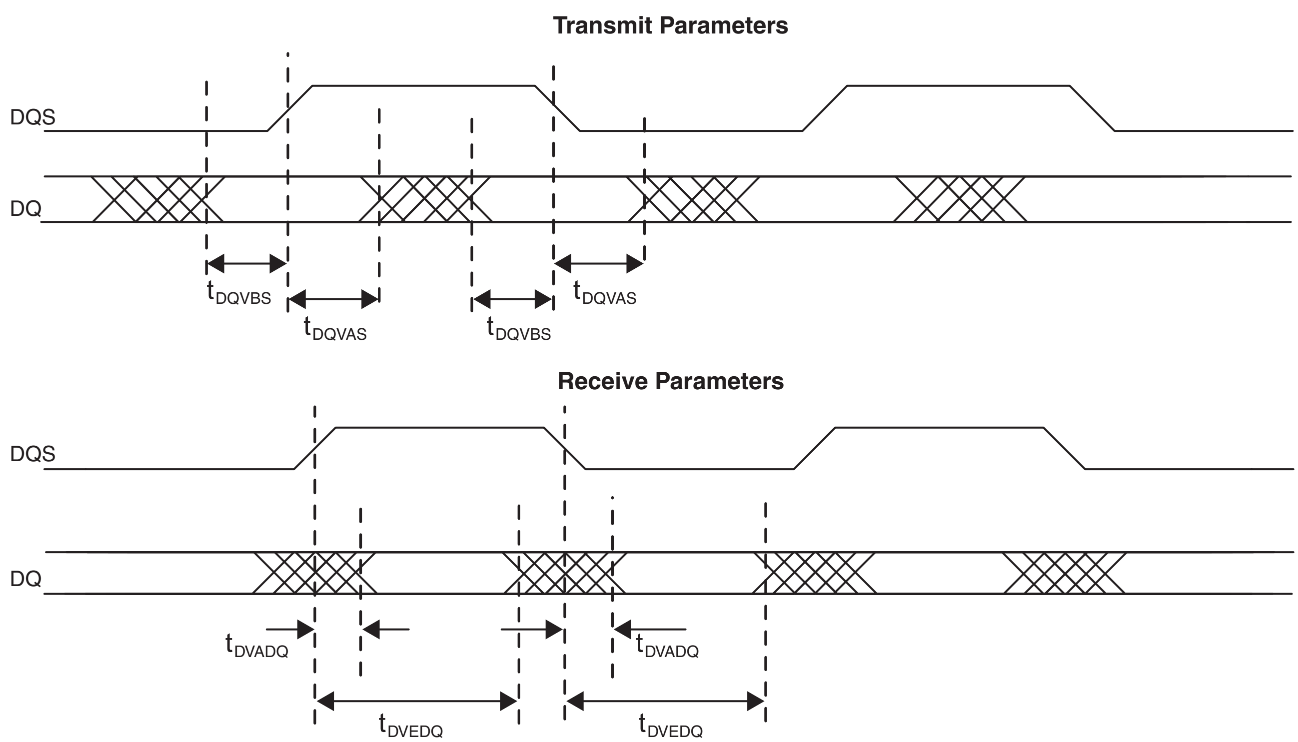


Figure 3-7. DDR/DDR2/DDR3 Parameters



LatticeECP3 Maximum I/O Buffer Speed (Continued)[1, 2, 3, 4, 5, 6]

Over Recommended Operating Conditions

Buffer	Description	Max.	Units
PCI33	PCI, V_{CCIO} = 3.3 V	66	MHz

1. These maximum speeds are characterized but not tested on every device.
2. Maximum I/O speed for differential output standards emulated with resistors depends on the layout.
3. LVCMOS timing is measured with the load specified in the Switching Test Conditions table of this document.
4. All speeds are measured at fast slew.
5. Actual system operation may vary depending on user logic implementation.
6. Maximum data rate equals 2 times the clock rate when utilizing DDR.

Figure 3-16. Jitter Transfer – 1.25 Gbps

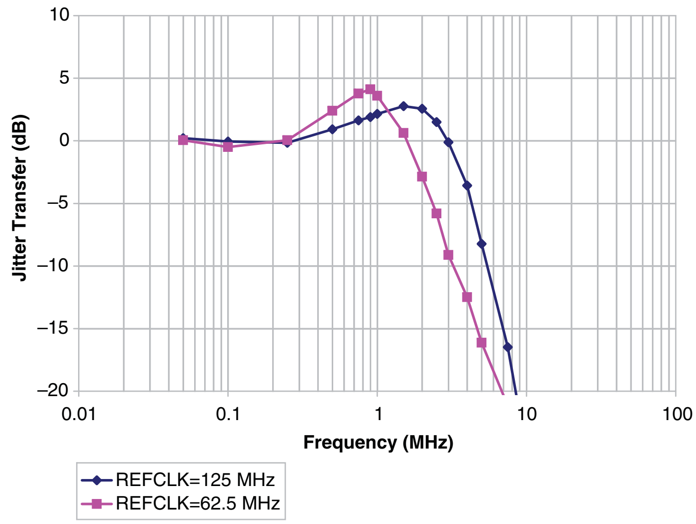
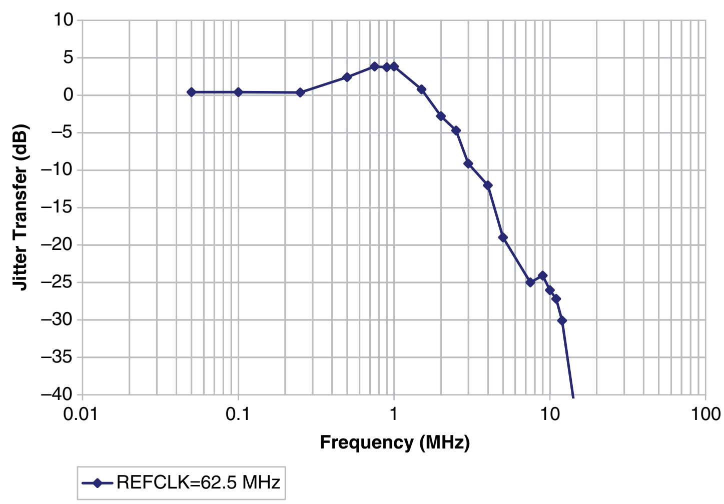


Figure 3-17. Jitter Transfer – 622 Mbps



HDMI (High-Definition Multimedia Interface) Electrical and Timing Characteristics

AC and DC Characteristics

Table 3-22. Transmit and Receive[1, 2]

Symbol	Description	Spec. Compliance		Units
		Min. Spec.	Max. Spec.	
Transmit				
Intra-pair Skew		—	75	ps
Inter-pair Skew		—	800	ps
TMDS Differential Clock Jitter		—	0.25	UI
Receive				
R_T	Termination Resistance	40	60	Ohms
V_{ICM}	Input AC Common Mode Voltage (50-Ohm Setting)	—	50	mV
TMDS Clock Jitter	Clock Jitter Tolerance	—	0.25	UI

1. Output buffers must drive a translation device. Max. speed is 2 Gbps. If translation device does not modify rise/fall time, the maximum speed is 1.5 Gbps.
2. Input buffers must be AC coupled in order to support the 3.3 V common mode. Generally, HDMI inputs are terminated by an external cable equalizer before data/clock is forwarded to the LatticeECP3 device.

Figure 3-28. Master SPI Configuration Waveforms

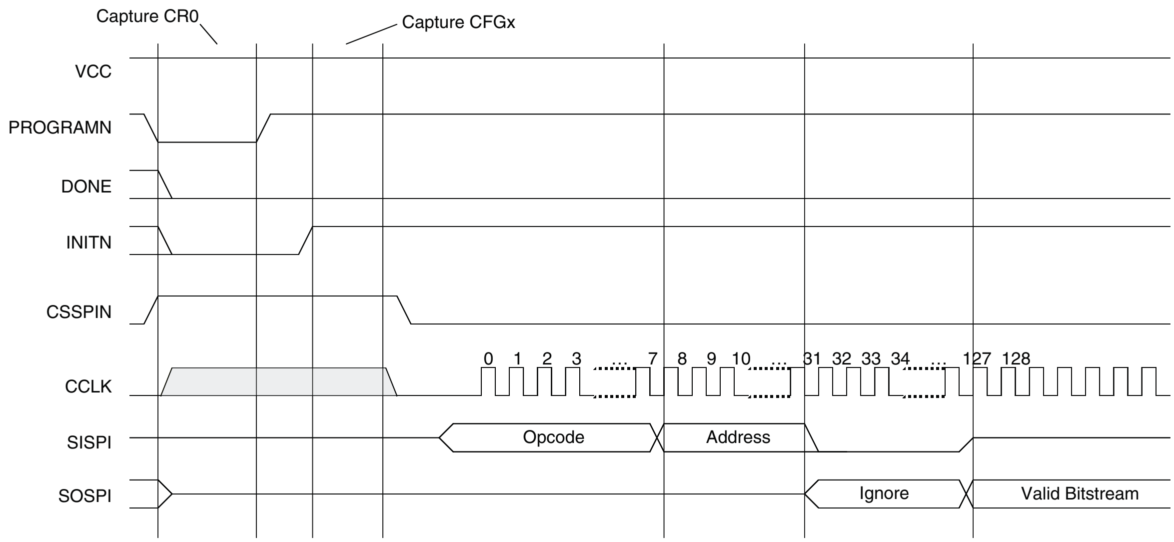
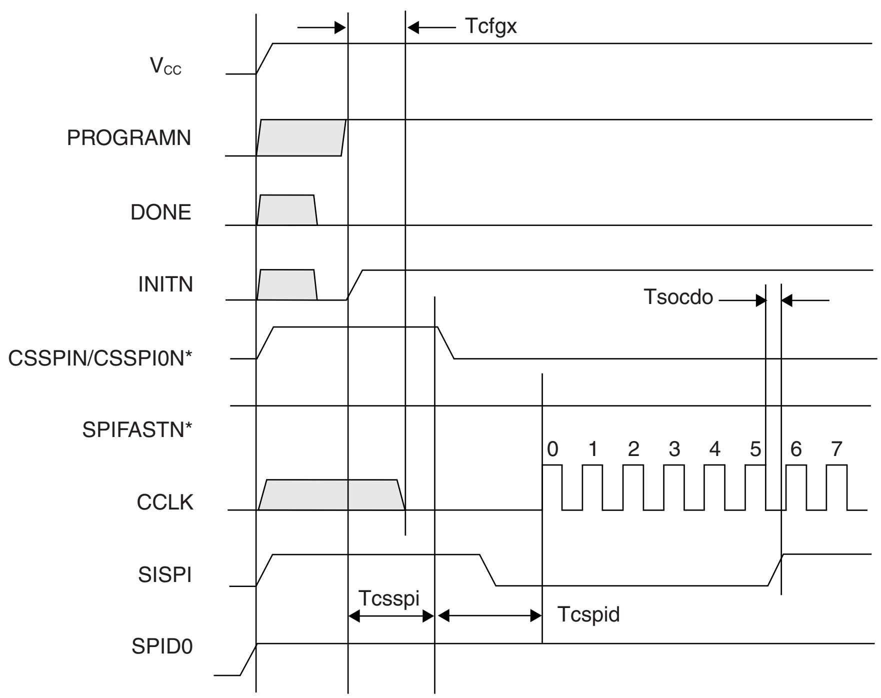


Figure 3-29. Master SPI POR Waveforms

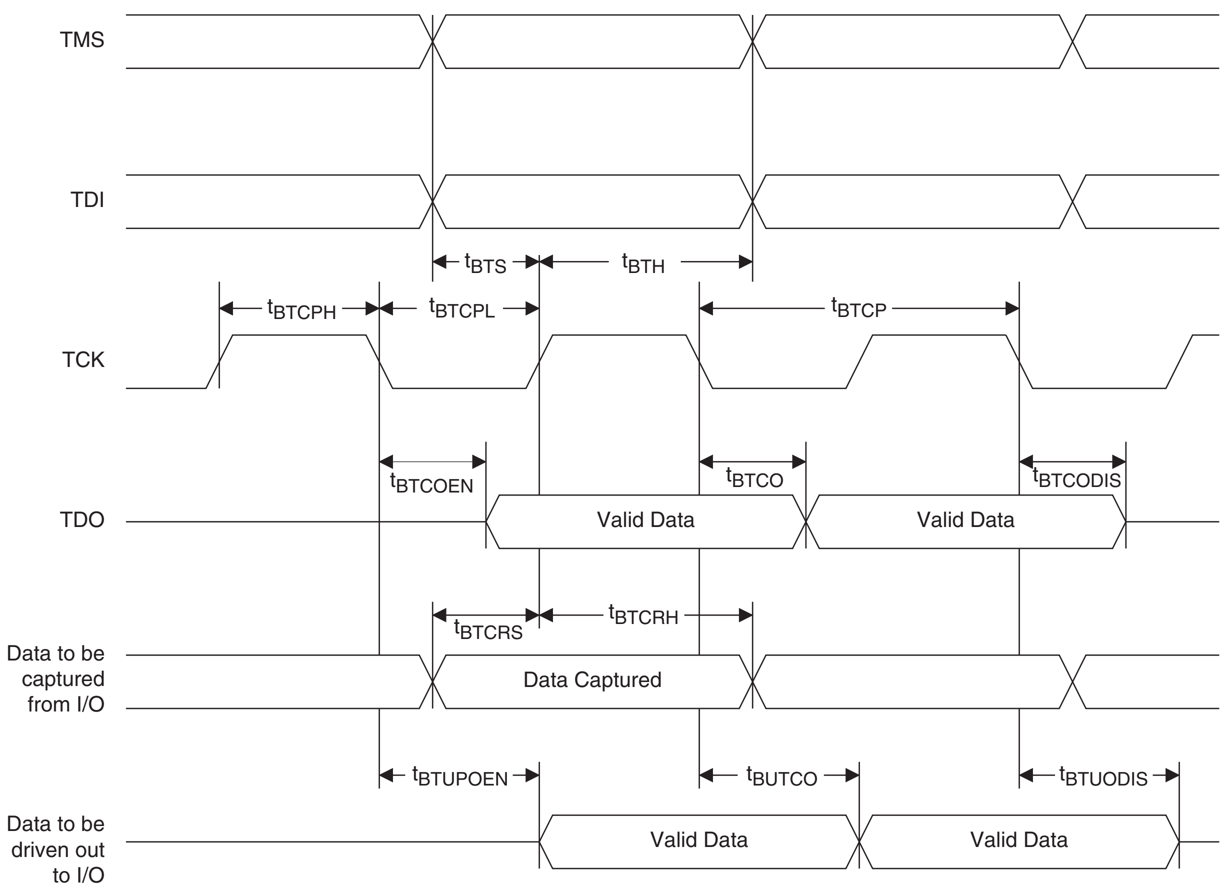


JTAG Port Timing Specifications

Over Recommended Operating Conditions

Symbol	Parameter	Min	Max	Units
f_{MAX}	TCK clock frequency	—	25	MHz
t_{BTCP}	TCK [BSCAN] clock pulse width	40	—	ns
t_{BTCPH}	TCK [BSCAN] clock pulse width high	20	—	ns
t_{BTCPL}	TCK [BSCAN] clock pulse width low	20	—	ns
t_{BTS}	TCK [BSCAN] setup time	10	—	ns
t_{BTH}	TCK [BSCAN] hold time	8	—	ns
t_{BTRF}	TCK [BSCAN] rise/fall time	50	—	mV/ns
t_{BTCO}	TAP controller falling edge of clock to valid output	—	10	ns
$t_{BTCODIS}$	TAP controller falling edge of clock to valid disable	—	10	ns
t_{BTCOEN}	TAP controller falling edge of clock to valid enable	—	10	ns
t_{BTCRS}	BSCAN test capture register setup time	8	—	ns
t_{BTCRH}	BSCAN test capture register hold time	25	—	ns
t_{BUTCO}	BSCAN test update register, falling edge of clock to valid output	—	25	ns
$t_{BTUODIS}$	BSCAN test update register, falling edge of clock to valid disable	—	25	ns
$t_{BTUPOEN}$	BSCAN test update register, falling edge of clock to valid enable	—	25	ns

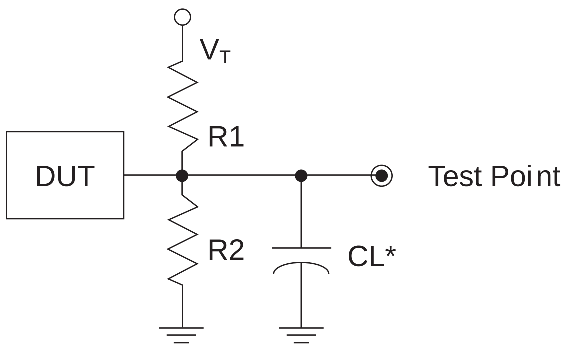
Figure 3-32. JTAG Port Timing Waveforms



Switching Test Conditions

Figure 3-33 shows the output test load that is used for AC testing. The specific values for resistance, capacitance, voltage, and other test conditions are shown in Table 3-23.

Figure 3-33. Output Test Load, LVTTL and LVCMOS Standards



*CL Includes Test Fixture and Probe Capacitance

Table 3-23. Test Fixture Required Components, Non-Terminated Interfaces

Test Condition	R_1	R_2	C_L	Timing Ref.	V_T
LVTTL and other LVCMOS settings (L -> H, H -> L)	∞	∞	0 pF	LVCMOS 3.3 = 1.5V	—
				LVCMOS 2.5 = $V_{CCIO}/2$	—
				LVCMOS 1.8 = $V_{CCIO}/2$	—
				LVCMOS 1.5 = $V_{CCIO}/2$	—
				LVCMOS 1.2 = $V_{CCIO}/2$	—
LVCMOS 2.5 I/O (Z -> H)	∞	1MΩ	0 pF	$V_{CCIO}/2$	—
LVCMOS 2.5 I/O (Z -> L)	1 MΩ	∞	0 pF	$V_{CCIO}/2$	V_{CCIO}
LVCMOS 2.5 I/O (H -> Z)	∞	100	0 pF	V_{OH} - 0.10	—
LVCMOS 2.5 I/O (L -> Z)	100	∞	0 pF	V_{OL} + 0.10	V_{CCIO}

Note: Output test conditions for all other interfaces are determined by the respective standards.

LatticeECP3 Devices, Green and Lead-Free Packaging

The following devices may have associated errata. Specific devices with associated errata will be notated with a footnote.

Commercial

Part Number	Voltage	Grade	Power	Package[1]	Pins	Temp.	LUTs (K)
LFE3-17EA-6FTN256C	1.2 V	–6	STD	Lead-Free ftBGA	256	COM	17
LFE3-17EA-7FTN256C	1.2 V	–7	STD	Lead-Free ftBGA	256	COM	17
LFE3-17EA-8FTN256C	1.2 V	–8	STD	Lead-Free ftBGA	256	COM	17
LFE3-17EA-6LFTN256C	1.2 V	–6	LOW	Lead-Free ftBGA	256	COM	17
LFE3-17EA-7LFTN256C	1.2 V	–7	LOW	Lead-Free ftBGA	256	COM	17
LFE3-17EA-8LFTN256C	1.2 V	–8	LOW	Lead-Free ftBGA	256	COM	17
LFE3-17EA-6MG328C	1.2 V	–6	STD	Green csBGA	328	COM	17
LFE3-17EA-7MG328C	1.2 V	–7	STD	Green csBGA	328	COM	17
LFE3-17EA-8MG328C	1.2 V	–8	STD	Green csBGA	328	COM	17
LFE3-17EA-6LMG328C	1.2 V	–6	LOW	Green csBGA	328	COM	17
LFE3-17EA-7LMG328C	1.2 V	–7	LOW	Green csBGA	328	COM	17
LFE3-17EA-8LMG328C	1.2 V	–8	LOW	Green csBGA	328	COM	17
LFE3-17EA-6FN484C	1.2 V	–6	STD	Lead-Free fpBGA	484	COM	17
LFE3-17EA-7FN484C	1.2 V	–7	STD	Lead-Free fpBGA	484	COM	17
LFE3-17EA-8FN484C	1.2 V	–8	STD	Lead-Free fpBGA	484	COM	17
LFE3-17EA-6LFN484C	1.2 V	–6	LOW	Lead-Free fpBGA	484	COM	17
LFE3-17EA-7LFN484C	1.2 V	–7	LOW	Lead-Free fpBGA	484	COM	17
LFE3-17EA-8LFN484C	1.2 V	–8	LOW	Lead-Free fpBGA	484	COM	17

1. Green = Halogen free and lead free.

Part Number	Voltage	Grade[1]	Power	Package	Pins	Temp.	LUTs (K)
LFE3-35EA-6FTN256C	1.2 V	–6	STD	Lead-Free ftBGA	256	COM	33
LFE3-35EA-7FTN256C	1.2 V	–7	STD	Lead-Free ftBGA	256	COM	33
LFE3-35EA-8FTN256C	1.2 V	–8	STD	Lead-Free ftBGA	256	COM	33
LFE3-35EA-6LFTN256C	1.2 V	–6	LOW	Lead-Free ftBGA	256	COM	33
LFE3-35EA-7LFTN256C	1.2 V	–7	LOW	Lead-Free ftBGA	256	COM	33
LFE3-35EA-8LFTN256C	1.2 V	–8	LOW	Lead-Free ftBGA	256	COM	33
LFE3-35EA-6FN484C	1.2 V	–6	STD	Lead-Free fpBGA	484	COM	33
LFE3-35EA-7FN484C	1.2 V	–7	STD	Lead-Free fpBGA	484	COM	33
LFE3-35EA-8FN484C	1.2 V	–8	STD	Lead-Free fpBGA	484	COM	33
LFE3-35EA-6LFN484C	1.2 V	–6	LOW	Lead-Free fpBGA	484	COM	33
LFE3-35EA-7LFN484C	1.2 V	–7	LOW	Lead-Free fpBGA	484	COM	33
LFE3-35EA-8LFN484C	1.2 V	–8	LOW	Lead-Free fpBGA	484	COM	33
LFE3-35EA-6FN672C	1.2 V	–6	STD	Lead-Free fpBGA	672	COM	33
LFE3-35EA-7FN672C	1.2 V	–7	STD	Lead-Free fpBGA	672	COM	33
LFE3-35EA-8FN672C	1.2 V	–8	STD	Lead-Free fpBGA	672	COM	33
LFE3-35EA-6LFN672C	1.2 V	–6	LOW	Lead-Free fpBGA	672	COM	33
LFE3-35EA-7LFN672C	1.2 V	–7	LOW	Lead-Free fpBGA	672	COM	33
LFE3-35EA-8LFN672C	1.2 V	–8	LOW	Lead-Free fpBGA	672	COM	33

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade[1]	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672I	1.2 V	–6	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-7FN672I	1.2 V	–7	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-8FN672I	1.2 V	–8	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-6LFN672I	1.2 V	–6	LOW	Lead-Free fpBGA	672	IND	149
LFE3-150EA-7LFN672I	1.2 V	–7	LOW	Lead-Free fpBGA	672	IND	149
LFE3-150EA-8LFN672I	1.2 V	–8	LOW	Lead-Free fpBGA	672	IND	149
LFE3-150EA-6FN1156I	1.2 V	–6	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-7FN1156I	1.2 V	–7	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-8FN1156I	1.2 V	–8	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-6LFN1156I	1.2 V	–6	LOW	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-7LFN1156I	1.2 V	–7	LOW	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-8LFN1156I	1.2 V	–8	LOW	Lead-Free fpBGA	1156	IND	149

1. For ordering information on -9 speed grade devices, please contact your Lattice Sales Representative.

Part Number	Voltage	Grade	Power	Package	Pins	Temp.	LUTs (K)
LFE3-150EA-6FN672ITW[1]	1.2 V	–6	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-7FN672ITW[1]	1.2 V	–7	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-8FN672ITW[1]	1.2 V	–8	STD	Lead-Free fpBGA	672	IND	149
LFE3-150EA-6FN1156ITW[1]	1.2 V	–6	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-7FN1156ITW[1]	1.2 V	–7	STD	Lead-Free fpBGA	1156	IND	149
LFE3-150EA-8FN1156ITW[1]	1.2 V	–8	STD	Lead-Free fpBGA	1156	IND	149

1. Specifications for the LFE3-150EA-*sp*FN*pkg*CTW and LFE3-150EA-*sp*FN*pkg*ITW devices, (where *sp* is the speed and *pkg* is the package), are the same as the LFE3-150EA-*sp*FN*pkg*C and LFE3-150EA-*sp*FN*pkg*I devices respectively, except as specified below.
   - The CTC (Clock Tolerance Circuit) inside the SERDES hard PCS in the TW device is not functional but it can be bypassed and implemented in soft IP.
   - The SERDES XRES pin on the TW device passes CDM testing at 250V.